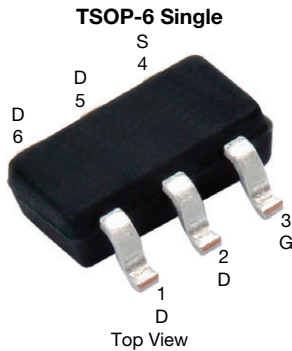


Automotive P-Channel 30 V (D-S) 175 °C MOSFET



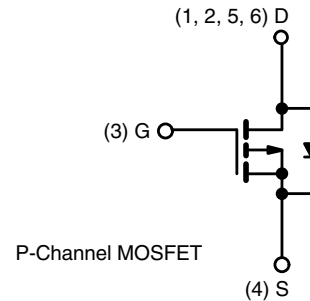
Marking Code: 9F

PRODUCT SUMMARY	
V_{DS} (V)	-30
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.021
$R_{DS(on)}$ (Ω) at $V_{GS} = -2.5$ V	0.033
I_D (A)	-8
Configuration	Single
Package	TSOP-6

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-30	V
Gate-source voltage		V_{GS}	± 12	
Continuous drain current	$T_C = 25$ °C	I_D	-8	A
	$T_C = 125$ °C		-7	
Continuous source current (diode conduction)		I_S	-4.5	
Pulsed drain current		I_{DM}	-32	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	-19.5	
Single pulse avalanche Energy		E_{AS}	19	
Maximum power dissipation ^a	$T_C = 25$ °C	P_D	5	W
	$T_C = 125$ °C		1.6	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R_{thJA}	110	°C/W
Junction-to-foot (drain)		R_{thJF}	30	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)



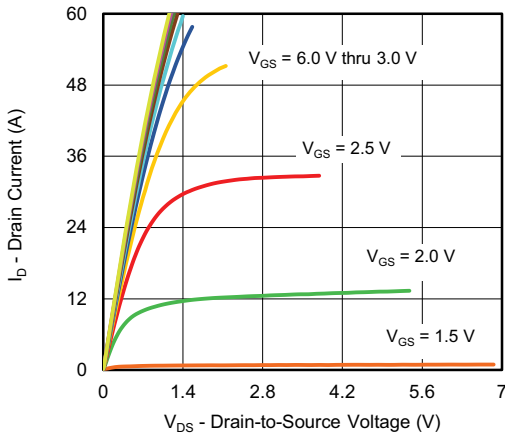
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		-30	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		-0.6	-1	-1.4	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = -30\text{ V}$	-	-	-1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = -30\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = -30\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}$	$V_{DS} = -5\text{ V}$	-10	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}$	$I_D = -5\text{ A}$	-	0.017	0.021	Ω
		$V_{GS} = -4.5\text{ V}$	$I_D = -5\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.030	
		$V_{GS} = -4.5\text{ V}$	$I_D = -5\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.034	
		$V_{GS} = -2.5\text{ V}$	$I_D = -4\text{ A}$	-	0.027	0.034	
Forward transconductance ^b	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -5\text{ A}$		-	24	-	S
Dynamic ^b							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = -20\text{ V}, f = 1\text{ MHz}$	-	3032	3950	pF
Output capacitance	C_{oss}			-	220	285	
Reverse transfer capacitance	C_{rss}			-	217	285	
Total gate charge ^c	Q_g	$V_{GS} = -4.5\text{ V}$	$V_{DS} = -15\text{ V}, I_D = -7.9\text{ A}$	-	29	41	nC
Gate-source charge ^c	Q_{gs}			-	5.7	-	
Gate-drain charge ^c	Q_{gd}			-	8.4	-	
Gate resistance	R_g	f = 1 MHz		2.2	5.6	9	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 1.9\text{ }\Omega$ $I_D \cong -7.9\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		-	20	28	ns
Rise time ^c	t_r			-	51	72	
Turn-off delay time ^c	$t_{d(off)}$			-	71	100	
Fall time ^c	t_f			-	68	96	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I_{SM}			-	-	-32	A
Forward voltage	V_{SD}	$I_F = -5\text{ A}, V_{GS} = 0\text{ V}$		-	-0.8	-1.2	V

Notes

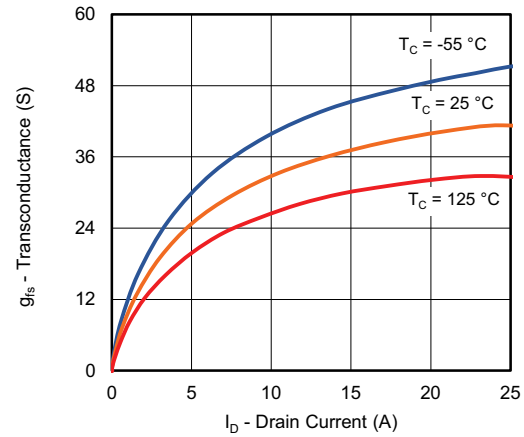
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production testing
- Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

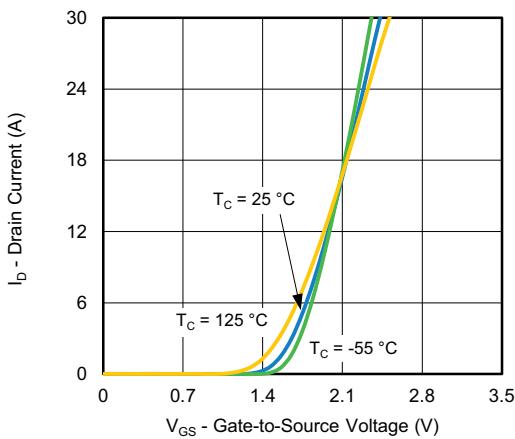
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



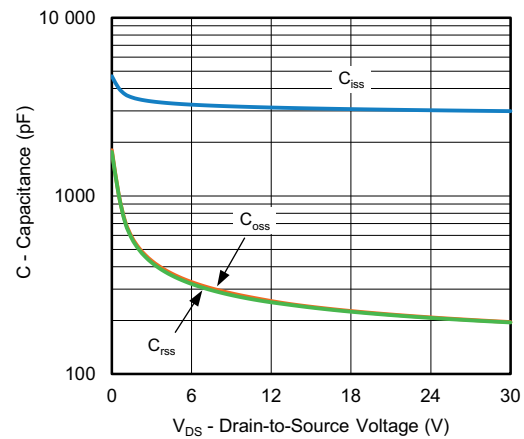
Output Characteristics



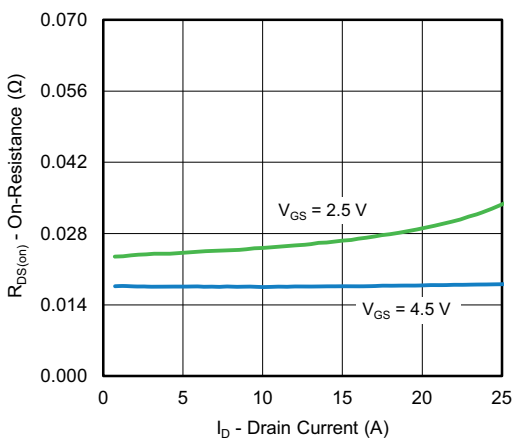
Transconductance



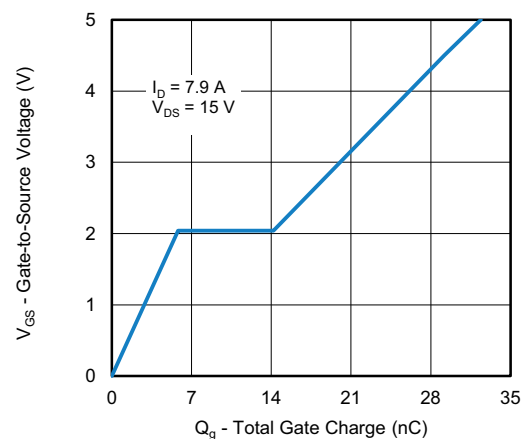
Transfer Characteristics



Capacitance



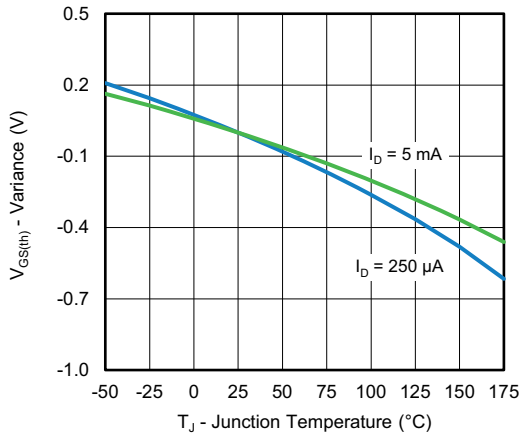
On-Resistance vs. Drain Current



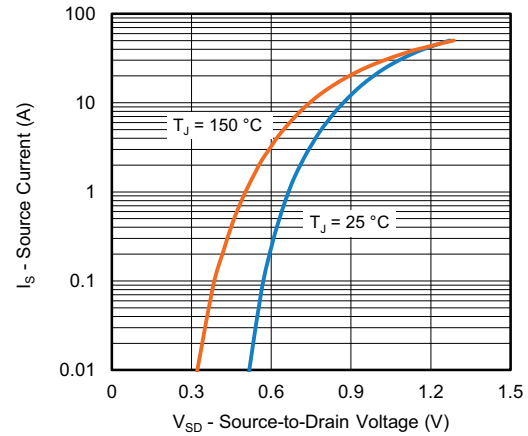
Gate Charge



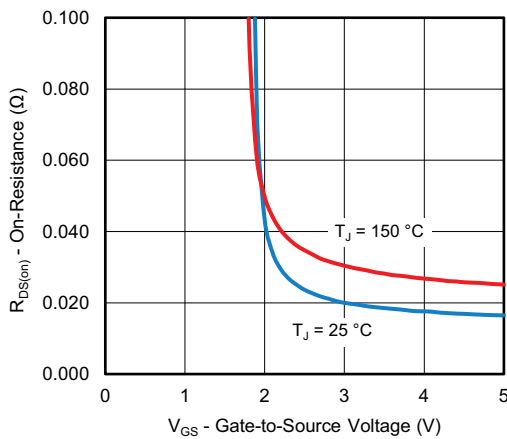
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



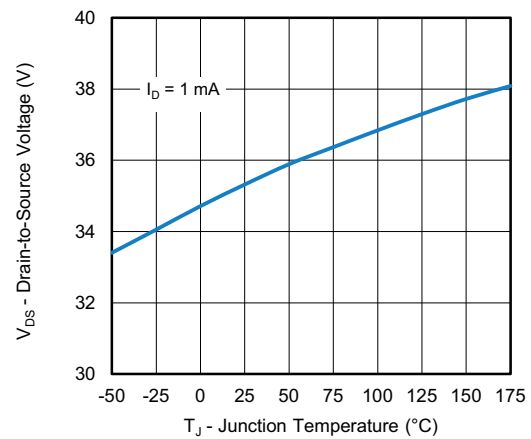
Threshold Voltage



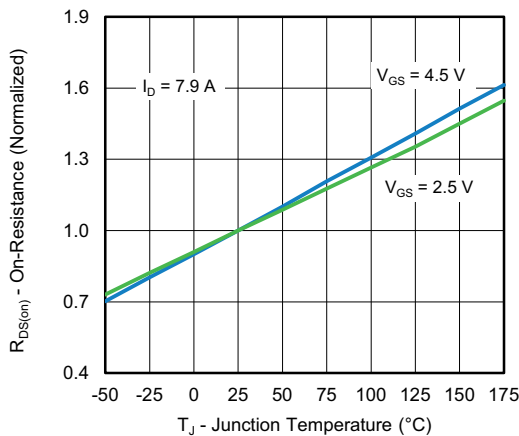
Source Drain Diode Forward Voltage



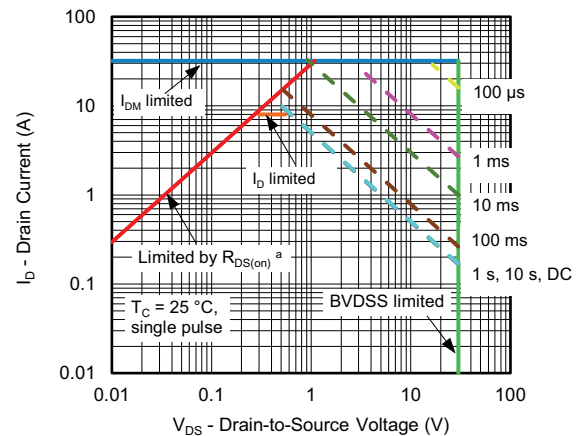
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Junction Temperature

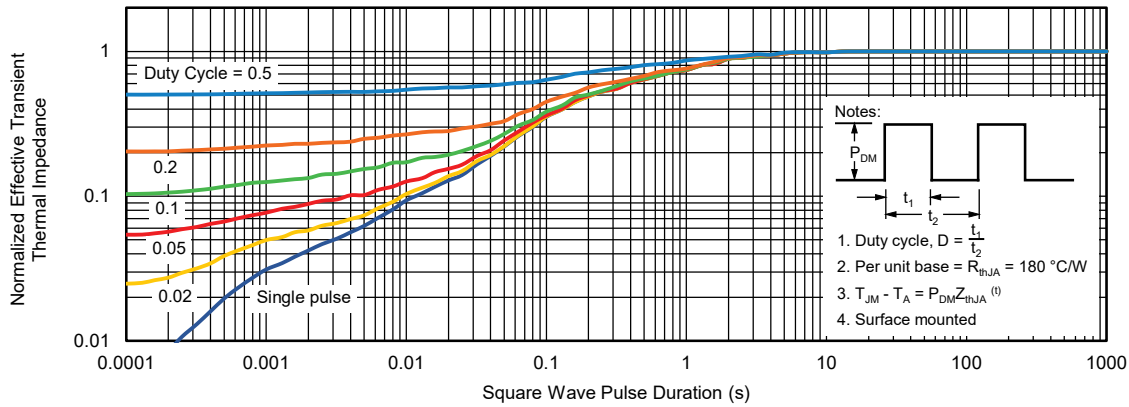


Safe Operating Area

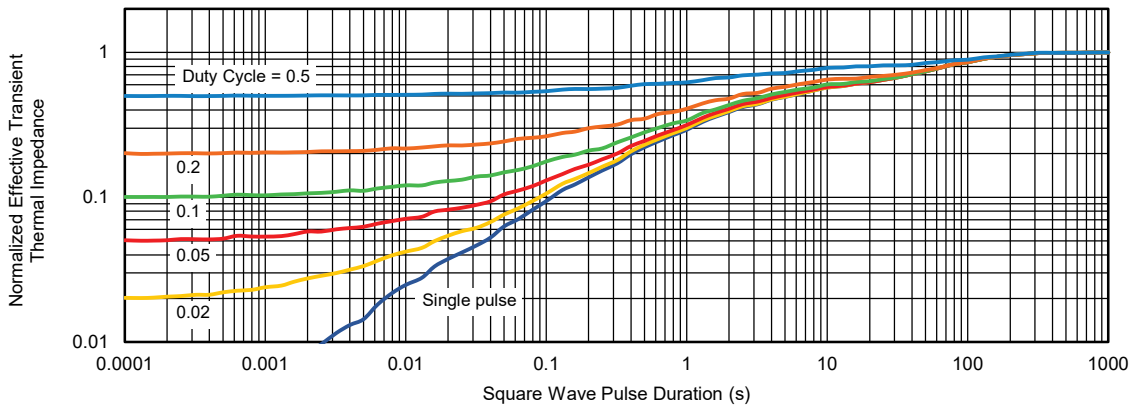
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

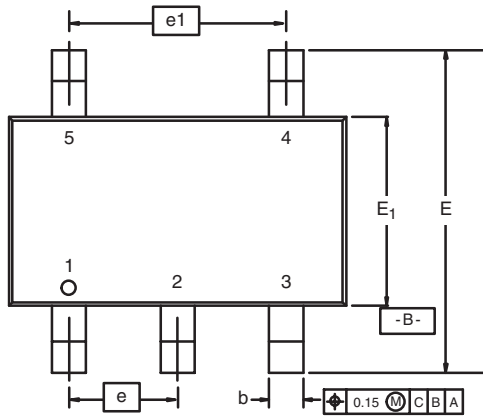
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

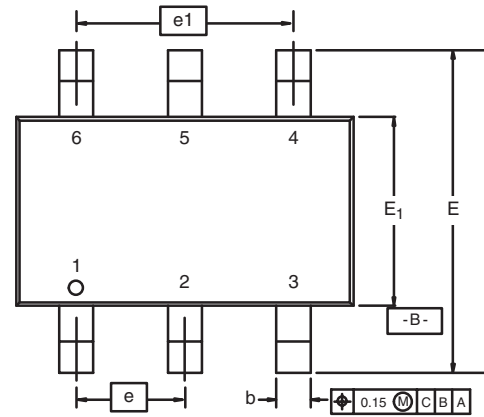
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TSOP: 5/6-LEAD

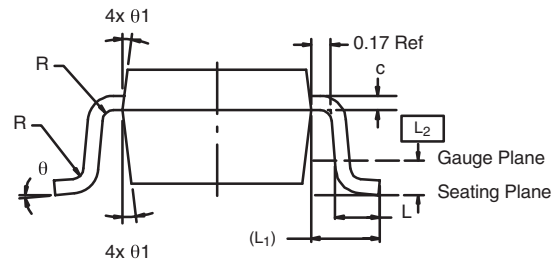
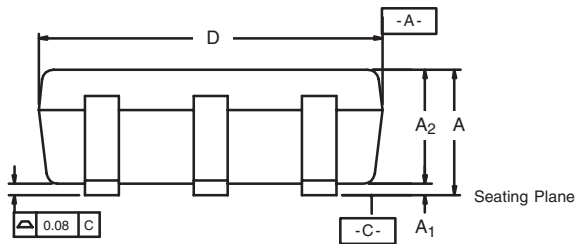
JEDEC Part Number: MO-193C



5-LEAD TSOP

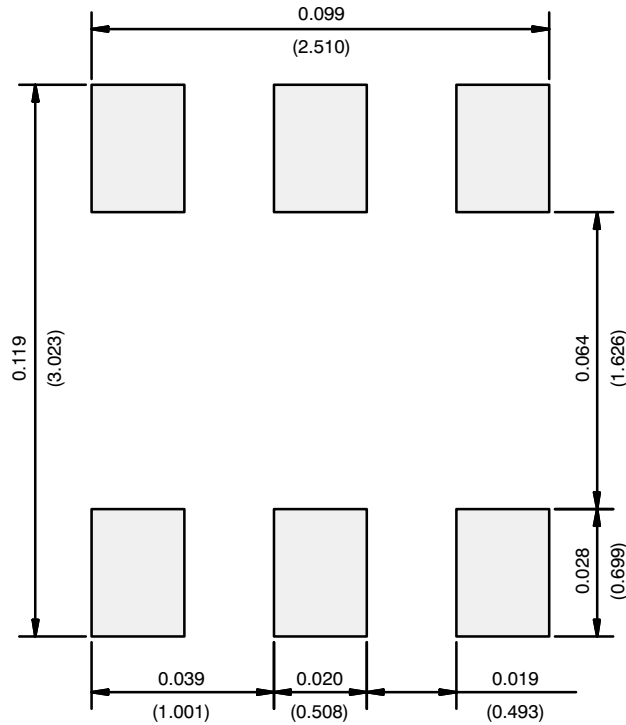


6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A₁	0.01	-	0.10	0.0004	-	0.004
A₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L₁	0.60 Ref			0.024 Ref		
L₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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